

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or unavteries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor and is officers, employees, uniotificated use, even if such claim any manner.



FDMC15N06 N-Channel UltraFET Power MOSFET

55 V, 15 A, 90 m Ω

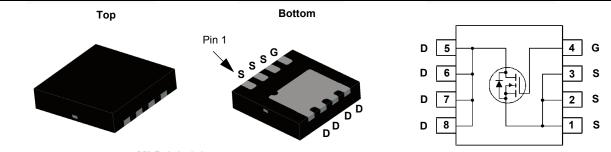
Features

- $R_{DS(on)}$ = 75 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 15 A
- 100% Avalanche Tested
- RoHS compliant

May 2014

Description

These N-Channel power MOSFETs are manufactured using the innovative UltraFET process. This advanced process technology achieves the lowest possible on-resistance per silicon area, resulting in outstanding performance. This device is capable of withstanding high energy in the avalanche mode and the diode exhibits very low reverse recovery time and stored charge. It was designed for use in applications where power efficiency is important, such as switching regulators, switching converters, motor drivers, relay drivers, lowvoltage bus switches, and power management in portable and battery-operated products.



MLP 3.3x3.3

MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol			FDMC15N06	Unit			
V _{DSS}	Drain to Source Voltage		55	V			
V _{GSS}	Gate to Source Voltage		±20	V			
I _D		- Continuous (T _C = 25 ^o C)		15			
	Drain Current	- Continuous (T _C = 100 ^o C)		9	Α		
		- Continuous ($T_A = 25^{\circ}C$)	(Note 1a)	2.4	Α		
DM	Drain Current	- Pulsed	(Note 2)	60	А		
AS	Single Pulsed Avalanche Energy (Note 3)			36	mJ		
AR	Avalanche Current		15	Α			
AR	Repetitive Avalanche Energy			3.5	mJ		
P _D	Devuer Dissinction	(T _C = 25°C)		35	W		
	Power Dissipation	$(T_{A} = 25^{\circ}C)$		2.3	W		
Г _Ј , Т _{STG}	Operating and Storage Te		-55 to +150	°C			
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C		

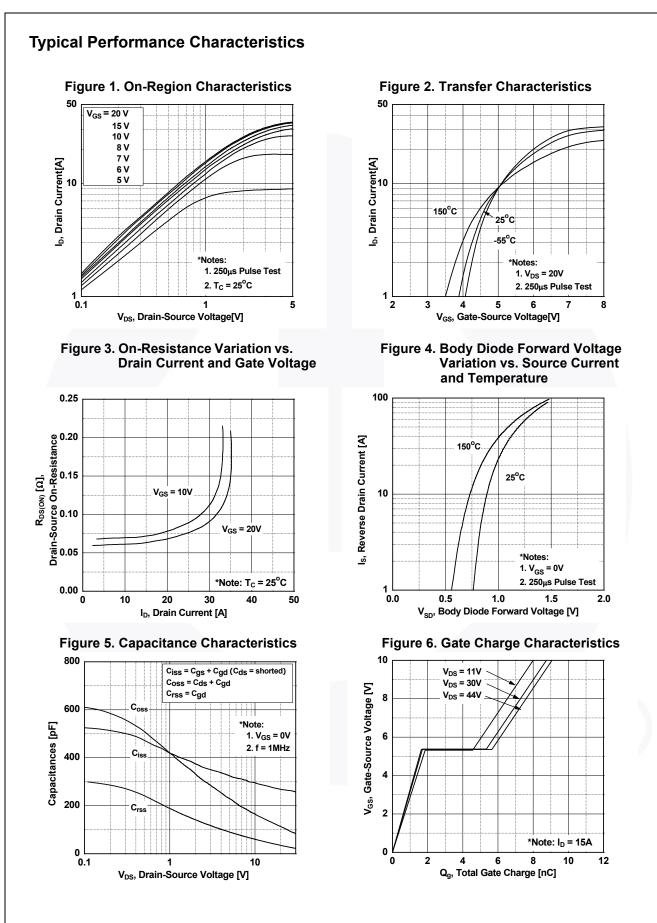
Thermal Characteristics

Symbol	Parameter	FDMC15N06	Unit	
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	3.5	°C/W	
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max. (Note 1a)	53	0/00	

Fart Null	nber	Top Mark	Pack	Package Packing Method		Reel Size	Tape Width		Qua	ntity
FDMC15N06		15N06	Powe	er 33	Tape and Reel	330 mm	1	2 mm	3000	units
Electrica	l Chara	acteristics T _C =2	25°C unles	ss othe	erwise noted.					
Symbol		Parameter			Test Condition	ons	Min.	Тур.	Max.	Unit
Off Charac	teristics	i								
BV _{DSS}	Drain to Source Breakdown Voltage			I _D	I_D = 250 µA, V_{GS} = 0 V, T_C = 25°C		55	-	-	V
∆BV _{DSS}	Breakdown Voltage Temperature		re	$I_D = 250 \ \mu$ A, Referenced to 25° C		_	70	_	V/ºC	
$/\Delta T_J$	Coefficie	nt						10		V/ U
I _{DSS}	Zero Gate Voltage Drain Current			$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}$			-	1	μA	
				$V_{DS} = 45 \text{ V}, T_{C} = 150^{\circ}\text{C}$			-	-	250	
GSS	Gate to Body Leakage Current			$V_{GS} = \pm 20 V, V_{DS} = 0 V$			-	-	±100	nA
On Charac	teristics									
V _{GS(th)}	Gate Threshold Voltage			V	V _{GS} = V _{DS} , I _D = 250 μA			-	4.0	V
R _{DS(on)}	Static Dr	Static Drain to Source On Resistance		Vc	V _{GS} = 10 V, I _D = 15 A			0.075	0.090	Ω
9 _{FS}	Forward	Forward Transconductance		V _{DS} = 20 V, I _D = 15 A			-	5	-	S
Dynamic C	haracte	ristics								
C _{iss}		pacitance					-	265	350	pF
C _{oss}		Capacitance			_{DS} = 25 V, V _{GS} = 0 V	_	_	97	130	pF
C _{rss}		Transfer Capacitance		f =	= 1 MHz	-	-	28	42	pF
Q _{g(tot)}		te Charge at 10V		V.	_{DS} = 30 V,I _D = 15 A,			8.8	11.5	nC
Q _{gs}		Source Gate Charge			$V_{GS} = 10 V$		-	1.7	-	nC
Q _{gd}		Drain "Miller" Charge				(Note 4)	-	3.6	-	nC
Switching	Charact	oristics							1	
t _{d(on)}		Delay Time	_				-	9.5	29	ns
- <u>a(on)</u> t _r		Rise Time			V _{DD} = 30 V, I _D = 15 A,		-	36.5	83	ns
t _{d(off)}		Delay Time			$V_{GS} = 10 V, R_G = 25 \Omega$		-	22.5	55	ns
t _f	Turn-Off	Turn-Off Fall Time			(Note 4)		-	22	54	ns
Drain Sour		e Characteristics				I		_		
					and Current				45	•
l _S					de Forward Current			-	15	A
ISM		n Pulsed Drain to Sour		1				-	60	A V
V _{SD}		Source Diode Forward	ard Voltage		$V_{GS} = 0 V, I_{SD} = 15 A$		-	- 20	1.25	
t _{rr}		Recovery Time Recovery Charge			_{GS} = 0 V, I _{SD} = 15 A, ₌/dt = 100 A/μs	(Note 5)	-	30 35	-	ns nC
Q _{rr}	Reveise	Recovery Charge		u	$dI_{F}/dt = 100 A/\mu s$		-	- 35	-	lic

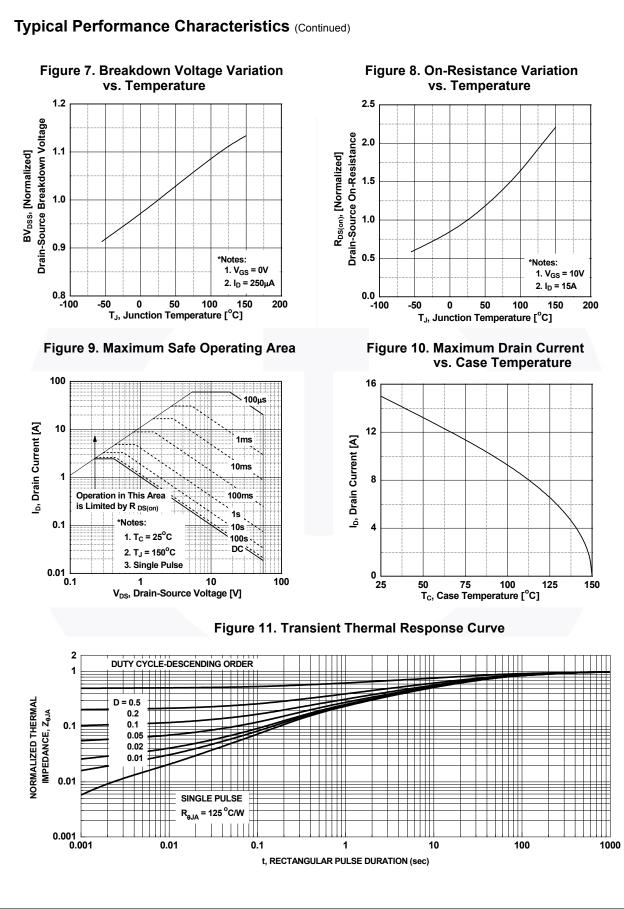
4: Essentially independent of operating temperature typical characteristics.

5: $I_{SD} \leq$ 15 A, di/dt \leq 200 A/µs, V_{DD} \leq 40 V, starting T_J = 25°C.

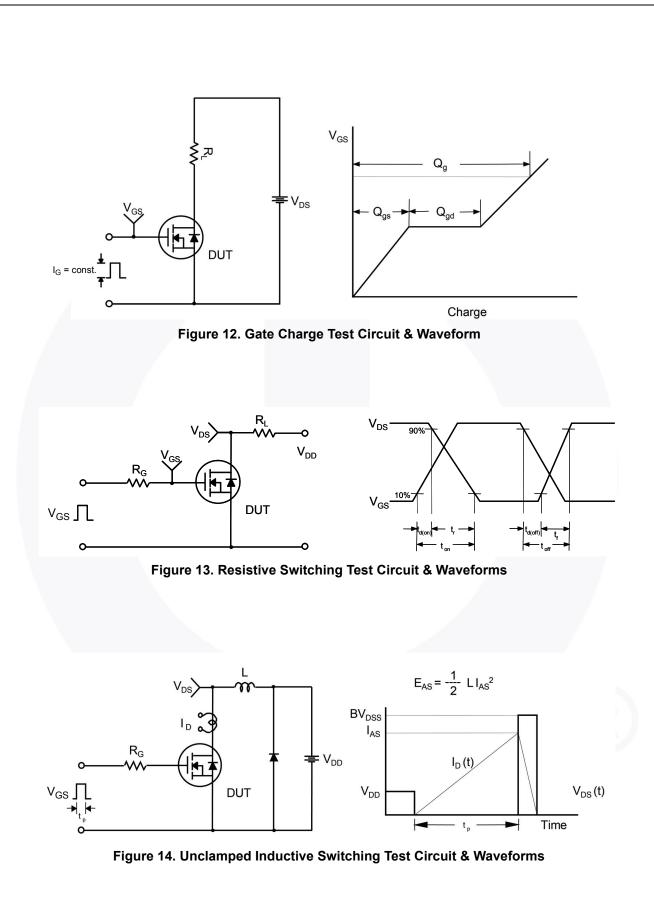


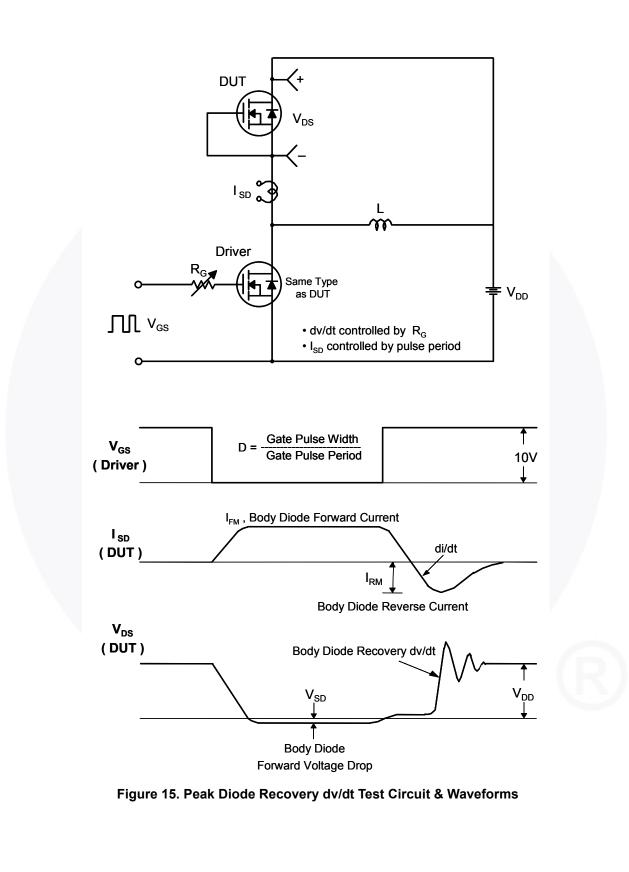
©2012 Fairchild Semiconductor Corporation FDMC15N06 Rev. C2

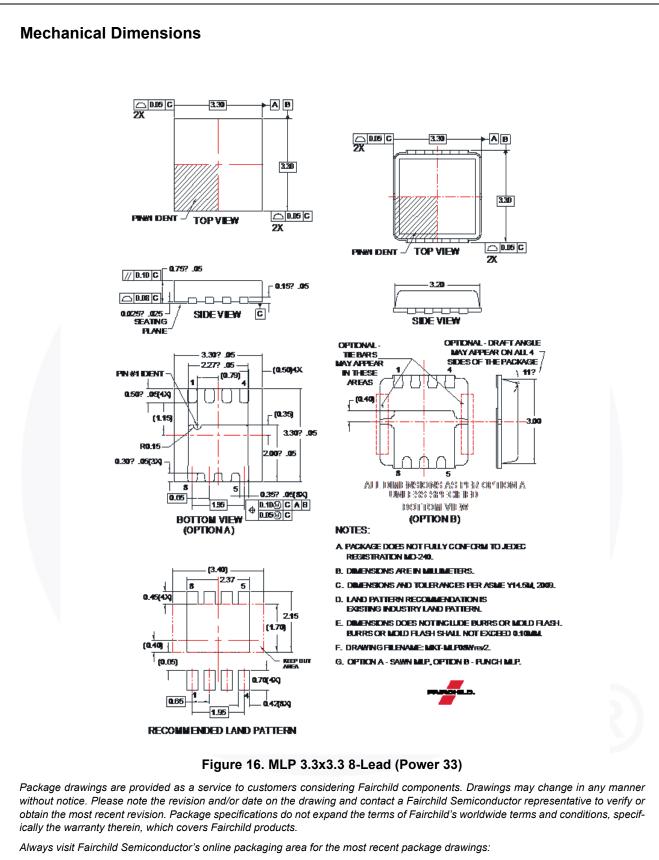
3



www.fairchildsemi.com







http://www.fairchildsemi.com/package/packageDetails.html?id=PN_MLJEU-C08



ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor haves against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death a

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below :

614233C 648584F IRFD120 JANTX2N5237 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L SBVS138LT1G 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C BUK954R8-60E NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE222 NTE2384 NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UF0-7B